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(71) Applicants *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, Chemin des Franques, F-38190 Bernin (FR). **COMMISSARIAT A L'ENERGIE ATOMIQUE** [FR/FR]; 31-33, rue de la Fédération, F-75015 Paris (FR).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **MAUNAND TUSSOT, Corinne** [FR/FR]; 1, avenue du Vercors, F-38240 Meylan (FR). **MALEVILLE, Christophe** [FR/FR]; 90, rue du Château, F-38660 La Terrasse (FR). **MORICEAU, Hubert** [FR/FR]; 26, rue Fournet, F-38120 Saint Egrève (FR). **SOUBIE, Alain** [FR/FR]; 3, rue Casimir Brenier, F-38120 Saint Egrève (FR).

(74) Agents: **MARTIN, Jean-Jacques,** et al.; Cabinet Regimbeau, 20, rue de Chazelles, F-75847 Paris Cedex 17 (FR).

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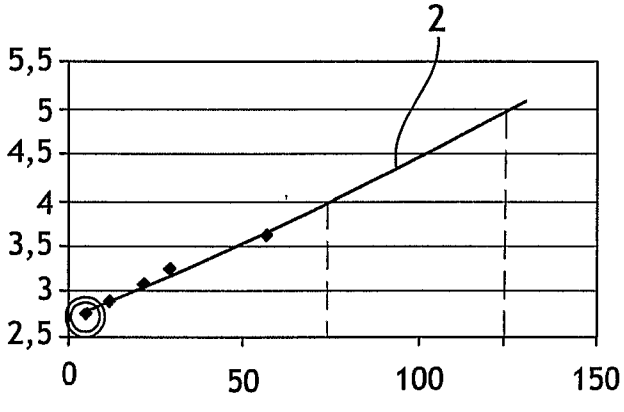
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(54) Title: PREPARING A SURFACE OF A SEMICONDUCTOR WAFER FOR BONDING WITH ANOTHER WAFER



(57) Abstract: The invention relates to a method for preparing an oxidised surface of a wafer for bonding with another wafer, the oxidised surface having been subject to an implantation of atomic species, the method including a first step of cleaning the oxidised surface by employing NH_4OH and H_2O_2, and a second step of cleaning by employing hydrochloric species (HCl), wherein the first step is implemented so as to etch from about 10 Å to about 120 Å, and wherein the second step is implemented at a selected temperature below around 50°C during about 10 minutes or less.

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